

Attorney Docket No. 040021-0307298
Client Reference: OPP 030894 US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: **GEON-OOK PARK**

Application No.:

Confirmation

No:

Filed: **December 19, 2003**

Group No.:

Examiner

For: **FORMATION METHOD OF GATE ELECTRODE IN SEMICONDUCTOR**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

APPLICATION DATA SHEET
37 C.F.R. § 1.76

BIBLIOGRAPHIC DATA

1. Applicant information

First applicant: **GEON-OOK PARK**
Citizenship: **Republic of Korea**
Residence: **Seoul, Korea**

2. Correspondence information

Correspondence for this application should be addressed as follows:

Customer No.: **00909**

3. Application information

Title of Invention: **FORMATION METHOD OF GATE ELECTRODE IN SEMICONDUCTOR**

Docket number assigned to this application: **040021-0307298**

Suggested Classification: **Class:**

Subclass:

Technology Center to which subject matter is assigned:

Total number of drawing sheets: **3**

Type of application:

Utility

Application is to be published. Suggested drawing figure for publication:

Secrecy order under § 5.2:

This application does not disclose subject matter of an application which is under a secrecy order pursuant to § 5.2.

4. Representative information

The following have a power of attorney or authorization of agent in this application:

Customer No.: 00909

5. Foreign priority information

Foreign priority is claimed for this application as follows:

Country: Republic of Korea
Application No.: 10-2002-0082001
Filing Date: December 20, 2002
Status: Pending

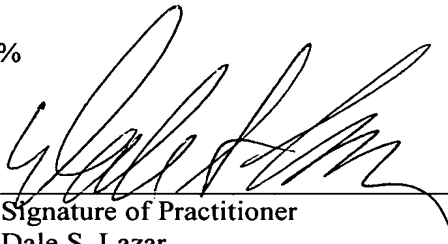
6. Assignee information

The assignee(s) of this application is/are:

Anam Semiconductor Inc.
891-10, Daechi-dong, Kangnam-ku
Seoul, 135-523
KOREA
Extent of interest of assignee in application: 100%

Date: December 19, 2003

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